



COPY

MICRON.009DV1

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Schuegraf et al.)
Appl. No. : 08/932,228)
Filed : September 17, 1997)
For : SHALLOW TRENCH ISOLATION)
USING LOW DIELECTRIC)
CONSTANT INSULATOR)
Examiner : Hung K. Vu)

Group Art Unit 2811

10/B
8/6/99
J. R. Kohn

AMENDMENT AND RESPONSE TO OFFICE ACTION

RECEIVED

APR 03 1999

Assistant Commissioner for Patents
Washington, D.C. 20231

TECHNOLOGY CENTER 2800

Dear Sir:

In response to the office action, mailed August 12, 1998, please amend the above-referenced application as indicated below.

IN THE CLAIMS:

11. (Amended) An isolation structure in a semiconductor substrate comprising:
a recessed portion formed therein in the semiconductor substrate; and
a dielectric material comprising a halide-doped silicon oxide filling the recessed portion,
said dielectric material having a dielectric constant lower than the dielectric constant of silicon dioxide.